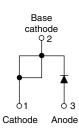


Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 16 A





PRODUCT SUMMARY								
Package	TO-220AC							
I _{F(AV)}	16 A							
V _R	1200 V							
V _F at I _F	2.3 V							
t _{rr} typ.	30 ns							
T _J max.	150 °C							
Diode variation	Single die							

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to JEDEC[®]-JESD47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA16TB120... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 16 A continuous current, the VS-HFA16TB120... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16TB120... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V _R		1200	V					
Maximum continuous forward current	١ _F	T _C = 100 °C	16						
Single pulse forward current	I _{FSM}		190	А					
Maximum repetitive forward current	I _{FRM}		64						
Maximum power dissipation	P _D	T _C = 25 °C	151	W					
Maximum power dissipation		T _C = 100 °C	60	vv					
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C					

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RoHS COMPLIANT

HALOGEN FREE Available



VS-HFA16TB120PbF, VS-HFA16TB120-N3

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ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		1200	-	-			
Maximum forward voltage		I _F = 16 A		-	2.5	3.0	v		
	V _{FM}	I _F = 32 A	See fig. 1	-	3.2	3.93			
		I _F = 16 A, T _J = 125 °C]	-	2.3	2.7			
Maximum reverse	I _{RM}	$V_{R} = V_{R}$ rated	See fig. 2	-	0.75	20			
leakage current		T_J = 125 °C, V_R = 0.8 x V_R rated	See lig. 2	-	375	2000	μA		
Junction capacitance	CT	V _R = 200 V See fig. 3		-	27	40	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body - 8.0				-	nH		

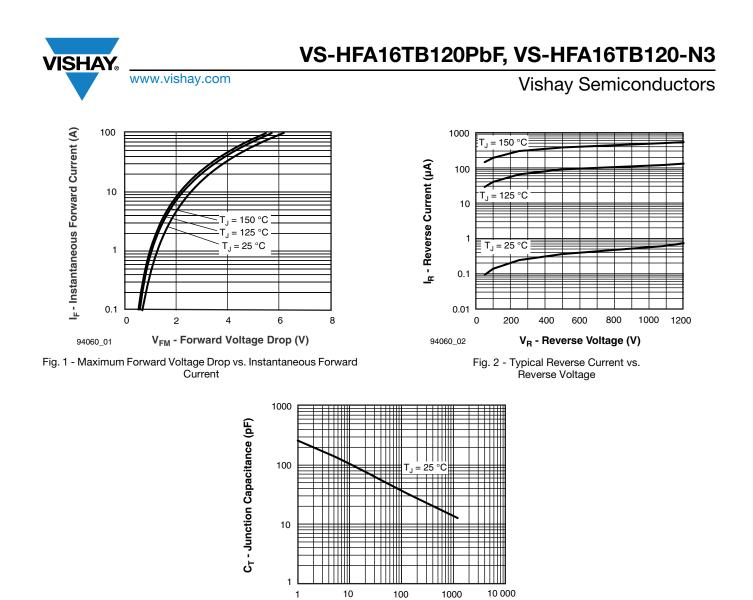
DYNAMIC RECOVERY CHARACTERISTICS (T_J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
D	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	30	-			
Reverse recovery time See fig. 5 and 10	t _{rr1}	T _J = 25 °C		-	90	135	ns		
occ lig. 5 and 10	t _{rr2}	T _J = 125 °C	I _F = 16 A dI _F /dt = 200 A/μs V _R = 200 V	-	164	245			
Peak recovery current See fig. 6	I _{RRM1}	T _J = 25 °C		-	5.8	10	A nC		
	I _{RRM2}	T _J = 125 °C		-	8.3	15			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	260	675			
See fig. 7	Q _{rr2}	T _J = 125 °C		-	680	1838			
Peak rate of fall of recovery current during t _b See fig. 8	dl _{(rec)M} /dt1	T _J = 25 °C		-	120	-	A/µs		
	dl _{(rec)M} /dt2	T _J = 125 °C		-	76	-	-ν μο		

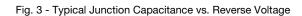
THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Thermal resistance, junction to case	R _{thJC}		-	-	0.83					
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	K/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.50	-					
Weight			-	2.0	-	g				
weight			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-220AC	HFA16TB120							

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V_R - Reverse Voltage (V)

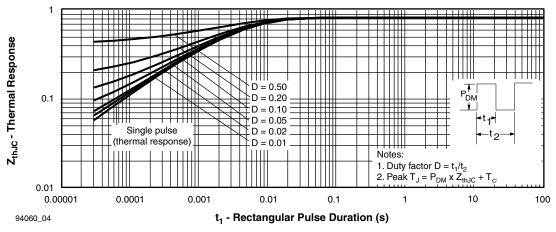


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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VS-HFA16TB120PbF, VS-HFA16TB120-N3

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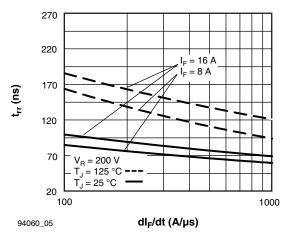


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

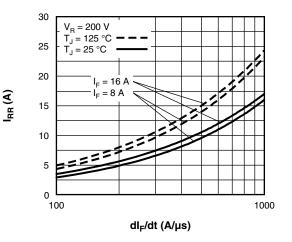


Fig. 6 - Typical Recovery Current vs. di_F/dt (Per Leg)

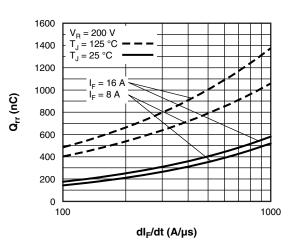


Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

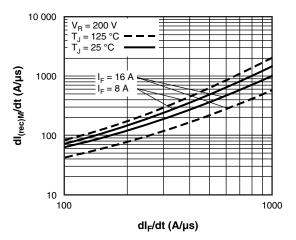


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt (Per Leg)

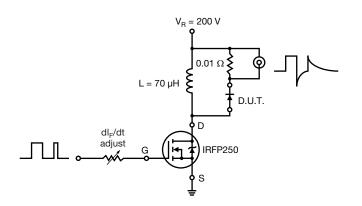


Fig. 9 - Reverse Recovery Parameter Test Circuit

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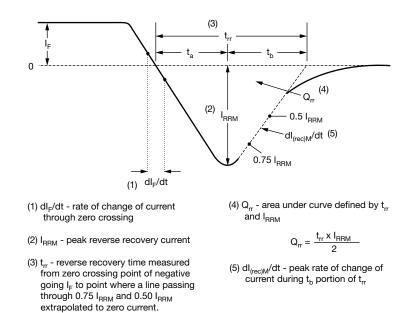
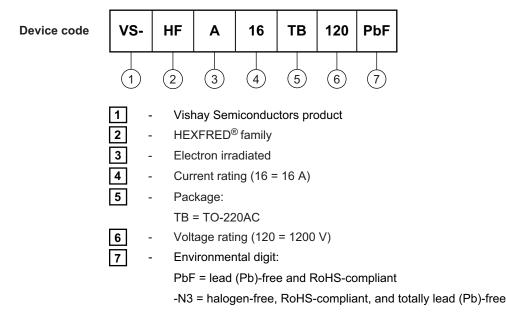


Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-HFA16TB120PbF	50	1000	Antistatic plastic tube						
VS-HFA16TB120-N3	50	1000	Antistatic plastic tube						

LINKS TO RELATED DOCUMENTS							
Dimensions		www.vishay.com/doc?95221					
Part marking information	TO-220ACPbF	www.vishay.com/doc?95224					
	TO-220AC-N3	www.vishay.com/doc?95068					

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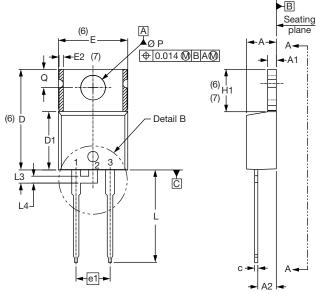


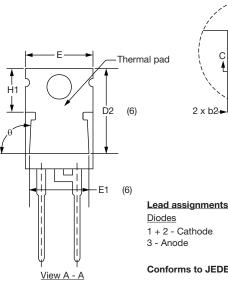
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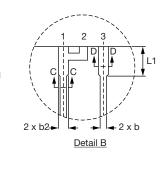
TO-220AC

plane

DIMENSIONS in millimeters and inches









Diodes 1 + 2 - Cathode 3 - Anode

Conforms to JEDEC outline TO-220AC

SYMBOL	MILLIM	IETERS	INC	HES	NOTES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBUL	MIN.	MAX.	MIN.	MAX.	NOTES		STNIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183			E1	6.86	8.89	0.270	0.350	6
A1	1.14	1.40	0.045	0.055			E2	-	0.76	-	0.030	7
A2	2.56	2.92	0.101	0.115			е	2.41	2.67	0.095	0.105	
b	0.69	1.01	0.027	0.040			e1	4.88	5.28	0.192	0.208	
b1	0.38	0.97	0.015	0.038	4		H1	6.09	6.48	0.240	0.255	6, 7
b2	1.20	1.73	0.047	0.068			L	13.52	14.02	0.532	0.552	
b3	1.14	1.73	0.045	0.068	4		L1	3.32	3.82	0.131	0.150	2
с	0.36	0.61	0.014	0.024			L3	1.78	2.13	0.070	0.084	
c1	0.36	0.56	0.014	0.022	4		L4	0.76	1.27	0.030	0.050	2
D	14.85	15.25	0.585	0.600	3		ØР	3.54	3.73	0.139	0.147	
D1	8.38	9.02	0.330	0.355			Q	2.60	3.00	0.102	0.118	
D2	11.68	12.88	0.460	0.507	6		θ	90° t	o 93°	90° t	o 93°	
E	10.11	10.51	0.398	0.414	3, 6							

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁴⁾ Dimension b1, b3 and c1 apply to base metal only
- ⁽⁵⁾ Controlling dimension: inches
- ⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2 and E1
- ⁽⁷⁾ Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- ⁽⁸⁾ Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline



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